

AMENDMENTS TO THE CLAIMS

Claims 1-7 (Cancelled)

8. (Currently Amended) An ESD protection component, comprising:

at least two MOS field effect transistors (FETs) of a first conductivity type, having two gates and formed in parallel on a first semiconductive layer having a second conductivity type; and

a first well having a first conductivity type, formed on the first semiconductive layer, comprising:

a connecting area, formed between the MOS FETs;

two parallel extension areas, formed perpendicular to the gates of the MOS FETs; and

a first doping area of the second conductivity type, formed in the connecting area;

wherein each of the MOS FETs has a drain region of the first conductivity type, and the drain regions are commonly and directly connected to a pad.

9. (Cancelled)

10. (New) The ESD protection component as claimed in claim 8,
wherein the first doping area is directly connected to the pad.

11. (New) The ESD protection component as claimed in claim 8,
wherein each of the MOS FETs has a source region of the first
conductivity type, and the source regions are commonly and directly
connected to a power rail.

12. (New) The ESD protection component as claimed in claim 8,
wherein the first well is electrically connected to the pad through
the extension areas.